

Important notice

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Kind regards,

Team Nexperia

DATA SHEET



BSV52

NPN switching transistor

Product data sheet
Supersedes data of 1999 Apr 15

2004 Jan 14

NPN switching transistor

BSV52

FEATURES

- Low current (max. 100 mA)
- Low voltage (max. 12 V).

APPLICATIONS

- High speed saturated switching applications, especially in portable equipment.

DESCRIPTION

NPN switching transistor in a SOT23 plastic package.

MARKING

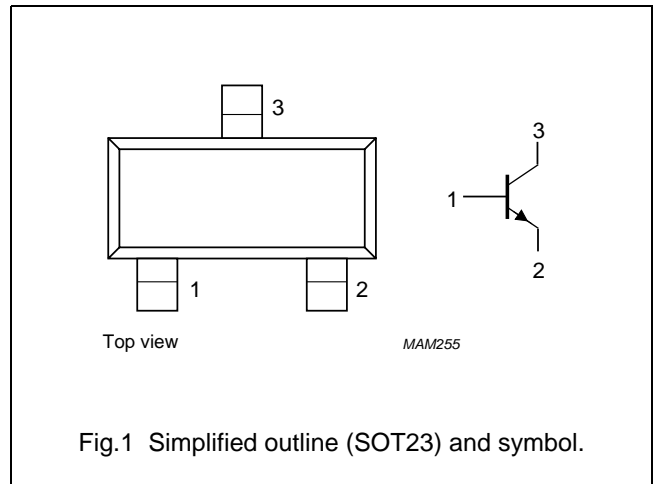
TYPE NUMBER	MARKING CODE ⁽¹⁾
BSV52	B2*

Note

- * = p : Made in Hong Kong.
 * = t : Made in Malaysia.
 * = W: Made in China.

PINNING

PIN	DESCRIPTION
1	base
2	emitter
3	collector



ORDERING INFORMATION

TYPE NUMBER	PACKAGE		
	NAME	DESCRIPTION	VERSION
BSV52	-	plastic surface mounted package; 3 leads	SOT23

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V _{CB0}	collector-base voltage	open emitter	-	20	V
V _{CEO}	collector-emitter voltage	open base	-	12	V
V _{EBO}	emitter-base voltage	open collector	-	5	V
I _C	collector current (DC)		-	100	mA
I _{CM}	peak collector current		-	200	mA
I _{BM}	peak base current		-	100	mA
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	-	250	mW
T _{stg}	storage temperature		-65	+150	°C
T _j	junction temperature		-	150	°C
T _{amb}	operating ambient temperature		-65	+150	°C

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THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$R_{th(j-a)}$	thermal resistance from junction to ambient	note 1	500	K/W

Note

1. Transistor mounted on an FR4 printed-circuit board.

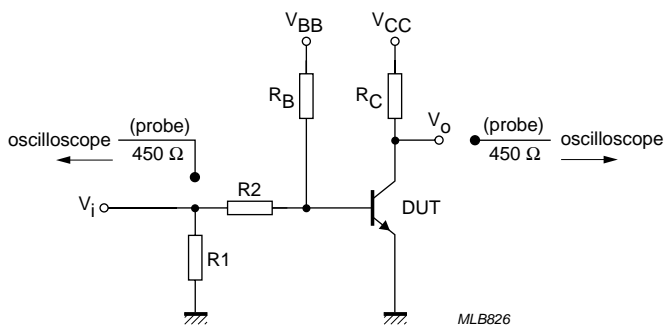
CHARACTERISTICS

$T_j = 25\text{ °C}$ unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I_{CBO}	collector cut-off current	$I_E = 0; V_{CB} = 20\text{ V}$	–	–	400	nA
		$I_E = 0; V_{CB} = 20\text{ V}; T_j = 125\text{ °C}$	–	–	30	μA
I_{EBO}	emitter cut-off current	$I_C = 0; V_{EB} = 4\text{ V}$	–	–	100	nA
h_{FE}	DC current gain	$V_{CE} = 1\text{ V}$				
		$I_C = 1\text{ mA}$	25	–	–	
		$I_C = 10\text{ mA}$	40	–	120	
		$I_C = 50\text{ mA}$	25	–	–	
V_{CEsat}	collector-emitter saturation voltage	$I_C = 10\text{ mA}; I_B = 300\text{ }\mu\text{A}$	–	–	300	mV
		$I_C = 10\text{ mA}; I_B = 1\text{ mA}$	–	–	250	mV
		$I_C = 50\text{ mA}; I_B = 5\text{ mA}$	–	–	400	mV
V_{BEsat}	base-emitter saturation voltage	$I_C = 10\text{ mA}; I_B = 1\text{ mA}$	700	–	850	mV
		$I_C = 50\text{ mA}; I_B = 5\text{ mA}$	–	–	1.2	V
C_c	collector capacitance	$I_E = i_e = 0; V_{CB} = 5\text{ V}; f = 1\text{ MHz}$	–	–	4	pF
C_e	emitter capacitance	$I_C = i_c = 0; V_{EB} = 1\text{ V}; f = 1\text{ MHz}$	–	–	4.5	pF
f_T	transition frequency	$I_C = 10\text{ mA}; V_{CE} = 10\text{ V}; f = 100\text{ MHz}$	400	500	–	MHz
Switching times (between 10% and 90% levels); (see Fig.2)						
t_{on}	turn-on time	$I_{Con} = 10\text{ mA}; I_{Bon} = 3\text{ mA};$ $I_{Boff} = -1.5\text{ mA}$	–	–	10	ns
t_d	delay time		–	–	4	ns
t_r	rise time		–	–	6	ns
t_{off}	turn-off time		–	–	20	ns
t_s	storage time		–	–	10	ns
t_f	fall time		–	–	10	ns

NPN switching transistor

BSV52



$V_i = 0.5 \text{ V to } 4.2 \text{ V}$; $T = 500 \mu\text{s}$; $t_p = 10 \mu\text{s}$; $t_r = t_s \leq 3 \text{ ns}$.
 $R1 = 56 \Omega$; $R2 = 1 \text{ k}\Omega$; $R_B = 1 \text{ k}\Omega$; $R_C = 270 \Omega$.
 $V_{BB} = 0.2 \text{ V}$; $V_{CC} = 2.7 \text{ V}$.
 Oscilloscope: input impedance $Z_i = 50 \Omega$.

Fig.2 Test circuit for switching times.

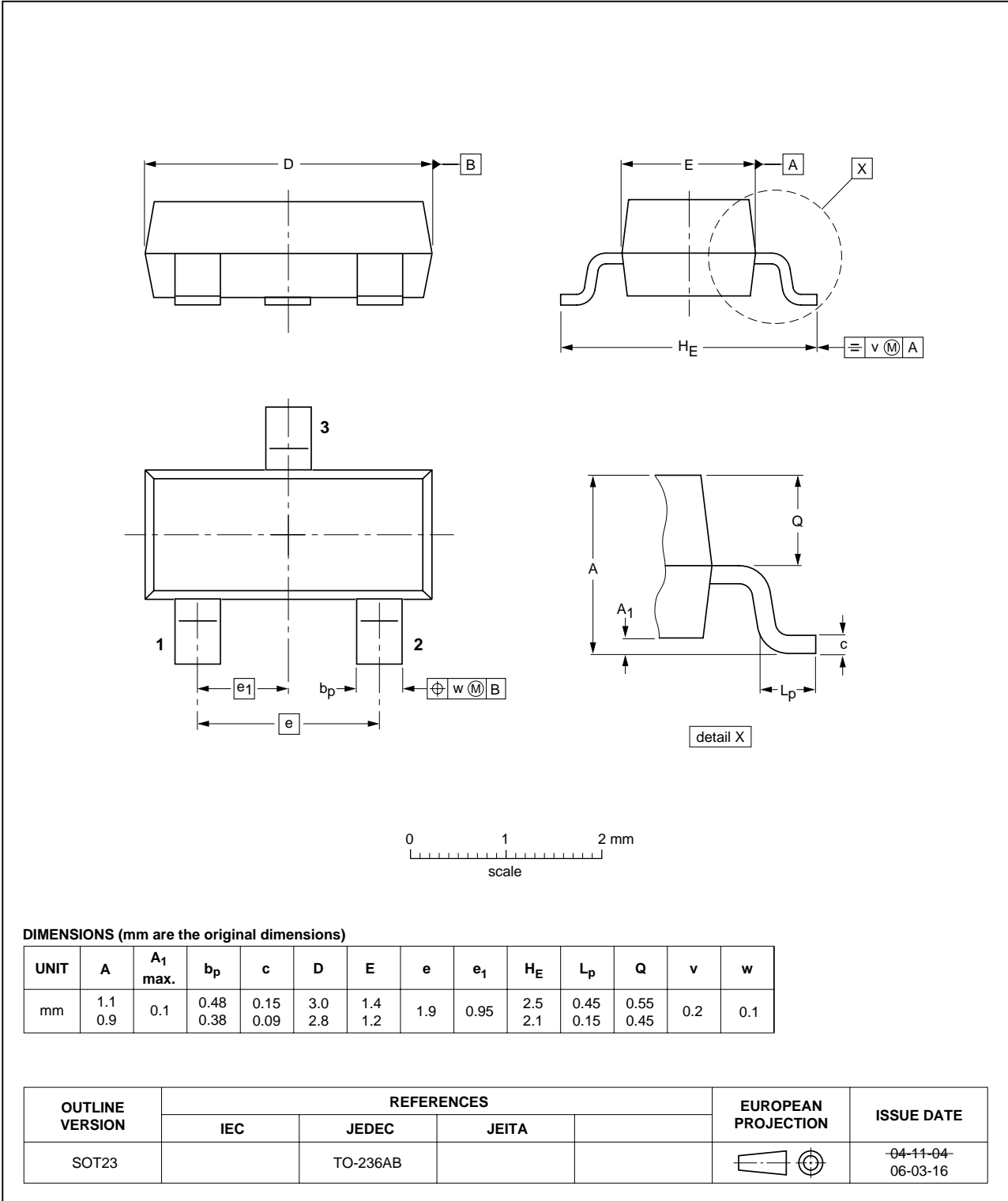
NPN switching transistor

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PACKAGE OUTLINE

Plastic surface-mounted package; 3 leads

SOT23



NPN switching transistor

BSV52

DATA SHEET STATUS

DOCUMENT STATUS ⁽¹⁾	PRODUCT STATUS ⁽²⁾	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

Notes

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2. The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL <http://www.nxp.com>.

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NXP Semiconductors

Customer notification

This data sheet was changed to reflect the new company name NXP Semiconductors, including new legal definitions and disclaimers. No changes were made to the technical content, except for package outline drawings which were updated to the latest version.

Contact information

For additional information please visit: <http://www.nxp.com>

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Printed in The Netherlands

R75/04/pp7

Date of release: 2004 Jan 14

Document order number: 9397 750 12431

